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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANTS Izumi FUSEGAWA et al.			
				FILING DATE February 13, 2006			
U.S. PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Name			
F.H.	1.	2003/0116082 A1	06/26/2003	Masahiro SAKURADA et al.			
F.H.	2.	2002/0157600 A1	10/31/2002	Izumi FUSEGAWA et al.			
FOREIGN PATENT DOCUMENTS							
Examiner Initials	Cite No.	Document Number	Date	Country	With English Abstract	With English Translation	
F.H.	3.	JP-A-2002-201093	07/16/2002	JAPAN	X	X	
	4.	WO 01/63027 A1	08/30/2001	WIPO	X		
	5.	WO 01/81661 A1	11/01/2001	WIPO	X		
	6.	JP-A-09-202684	08/05/1997	JAPAN	X	X	
	7.	JP-A-07-041383	02/10/1995	JAPAN	X	X	
	8.	JP-A-08-330316	12/13/1996	JAPAN	X	X	
	9.	JP-A-11-147786	06/02/1999	JAPAN	X	X	
F.H.	10.	JP-A-2000-327485	11/28/2000	JAPAN	X	X	
OTHER DOCUMENTS							
Examiner Initials	Cite No.	(Including Author, Title, Date, Pertinent Pages, etc.)					
F.H.	11.	Makoto TAKIYAMA et al.; "Dielectric Degradation of Silicon Dioxide Films Caused by Metal Contaminations"; <i>Ultra Clean Technology</i> ; Vol. 5, No. 5/6; Nippon Steel Corporation; pp. 345-359. (with abstract)					
EXAMINER						DATE CONSIDERED 6/8/2007	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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